

# 7/Amend B  
1. Sept 10  
11/10

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

ROBERT H. HAVEMANN ET AL.

Serial No. 09/216,214 (TI-21570)

Filed December 18, 1998

For: ENHANCEMENT TO POLYSILICON GATE

Art Unit 2811

Examiner T. Tran



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Assistant Commissioner for Patents  
Washington, D. C. 20231

Sir:

**AMENDMENT UNDER 37 C.F.R. 1.115**

In response to the Office action dated September 10, 1999, please amend the above identified application as follows:

**In the claims:**

Cancel claims 1 and 2 without prejudice.

Rewrite claim 8 as follows:

8. (Amended) A product by the method [of Claim 3] forming a transistor structure,

comprising the steps of:

(a) forming a dielectric over a semiconductor region;

(b) forming a patterned gate over said dielectric;

Sub D<sup>2</sup>  
Gent